METHOD FOR FABRICATING LONGITUDINALLY-SHAPED STRUCTURES

Abstract

There is provided a method to fabricate longitudinally-shaped structures, the method comprising a) providing a substrate selected to promote epitaxial growth thereon a selected growth orientation, b) depositing a crystalline sacrificial layer on the substrate for epitaxially growing along the selected growth orientation, c) forming a film over the sacrificial layer, the film having a crystal lattice structure grown substantially along the selected growth orientation, and d) removing at least part of the sacrificial layer, thereby producing the longitudinally shaped structures from the film by strain redistribution through the crystal lattice structure of the film to crack the film along a selected in-plane axis of the selected growth orientation.

Fig. 1